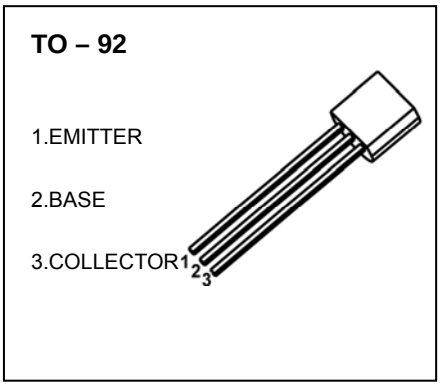
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

KSA539 TRANSISTOR (PNP)



FEATURES

- Low Saturation Medium Current Application
- Complement to KSC815

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	400	mW
$R_{\theta JA}$	Thermal Resistance From Junction To ambient	312	℃/W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=- 0.1mA,I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-45			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-45V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-3V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-1V, I_C=-50mA	40		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-150mA,I_B=-15mA			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-150mA,I_B=-15mA			-1.2	V
Base-emitter voltage	V_{BE}	V_{CE}=-1V, I_C=-10mA	-0.6		-0.9	V

CLASSIFICATION OF h_{FE}

RANK	R	O	Y
RANGE	40-80	70-140	120-240

A,Dec,2010